

Abstract of the Disclosure (Fig. 1)**A METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE**

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For manufacturing a semiconductor device having a polycrystalline film with large grains and a high crystallized volume fraction on an insulating substrate, a method is suggested which comprises forming a noncrystalline semiconductor layer (102) mainly composed of silicon on an insulating material (101), performing a first thermal treatment for a solid phase recrystallization on said noncrystalline semiconductor layer, raising the temperature during a certain time to a prescribed temperature higher than a temperature of said first thermal treatment, and performing a second thermal treatment.

This Sheet Has Been Replaced